

RJK2055DPA

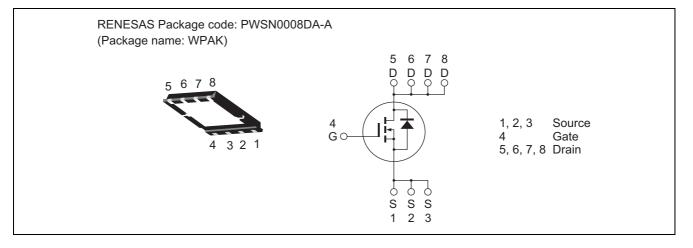
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1735-0200 Rev.2.00 Dec 24, 2008

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
ltem	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	20	А
Drain peak current	Note1 I _{D (pulse)}	40	А
Body-drain diode reverse drain current	I _{DR}	20	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	40	А
Avalanche current	I _{AP} ^{Note3}	9	А
Avalanche energy	E _{AR} ^{Note3}	5.4	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

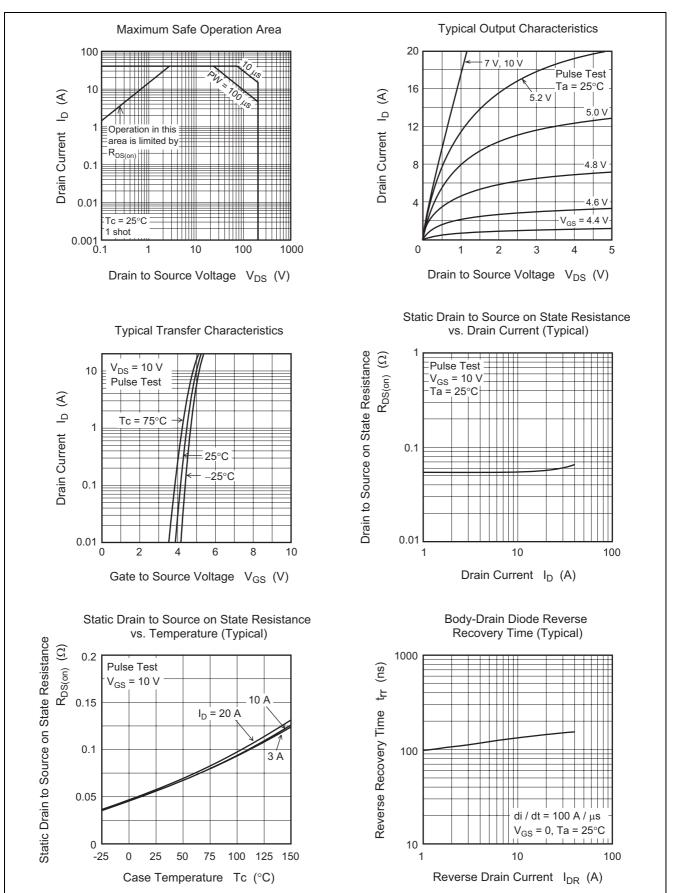
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

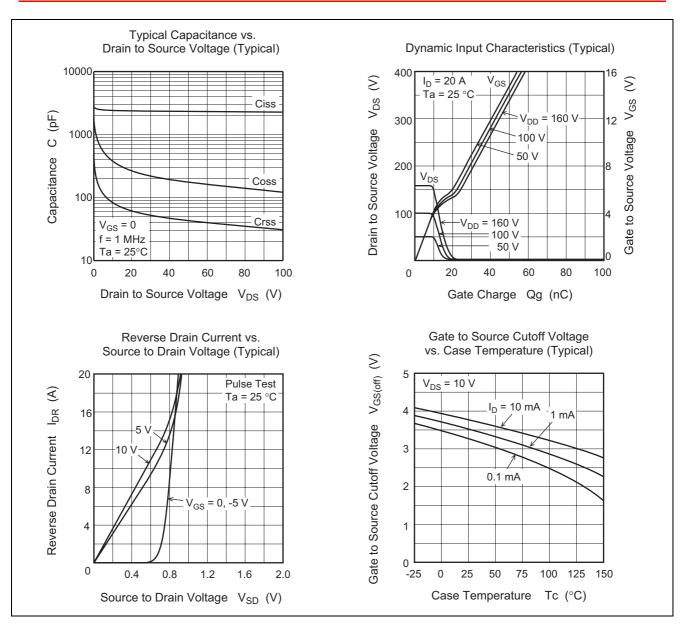
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	200	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	—	—	1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	±1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.054	0.069	Ω	$I_D = 10 \text{ A}, \text{ V}_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2400	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	245	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	55	_	pF	
Turn-on delay time	t _{d(on)}	_	30	_	ns	I _D = 10 A
Rise time	tr	_	50	_	ns	$V_{GS} = 10 V$ $R_L = 10 \Omega$ $Rg = 10 \Omega$
Turn-off delay time	t _{d(off)}	_	54		ns	
Fall time	t _f	_	37		ns	
Total gate charge	Qg	_	38	_	nC	V _{DD} = 160 V
Gate to source charge	Qgs	_	11.5	_	nC	V _{GS} = 10 V I _D = 20 A
Gate to drain charge	Qgd	_	9	—	nC	
Body-drain diode forward voltage	V _{DF}	_	0.91	1.40	V	$I_F = 20 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}		145	_	ns	$I_F = 20 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

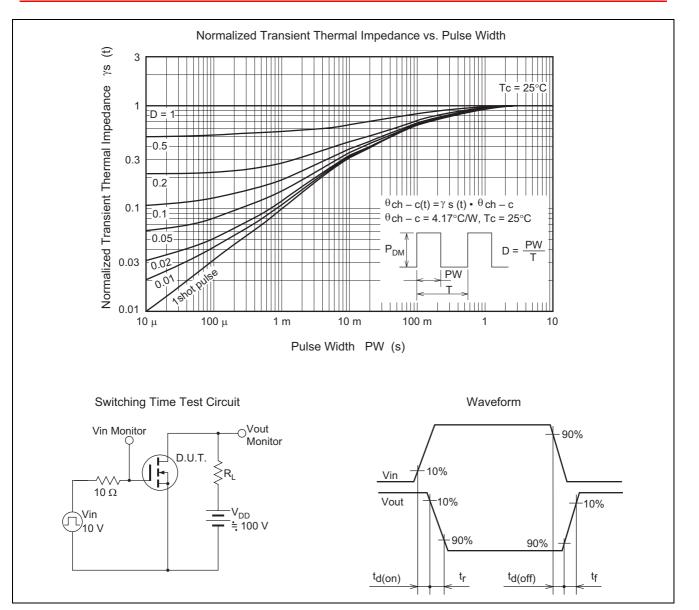
Main Characteristics



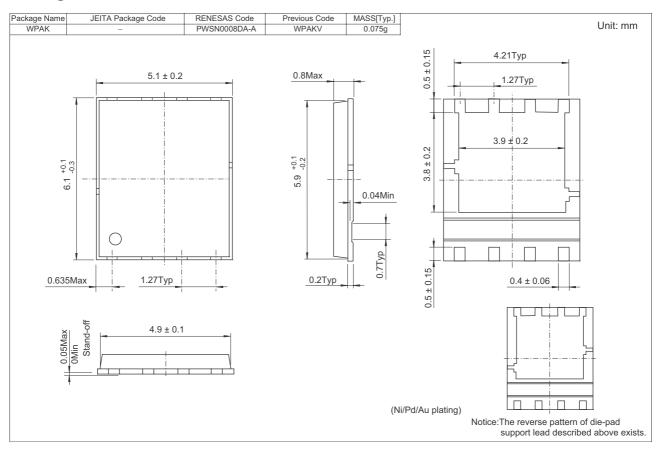
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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2055DPA-00-J0	2500 pcs	Taping

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